

## HIGH POWER NPN SILICON TRANSISTORS

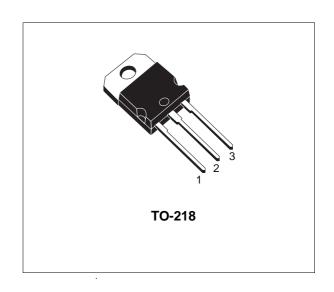
- STMicroelectronics PREFERRED SALESTYPES
- NPN TRANSISTOR
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- VERY LOW SATURATION VOLTAGE AND HIGH GAIN

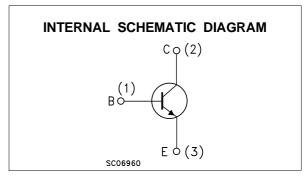
#### **APPLICATION**

- SWITCHING REGULATORS
- MOTOR CONTROL
- HIGH FREQUENCY AND EFFICENCY CONVERTERS

#### **DESCRIPTION**

The BUW48 and BUW49 are Multi-Epitaxial Planar NPN transistor in TO-218 plastic package. They are intented for use in high frequency and efficiency converters such us motor controllers and industrial equipment.





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Va	Value		
		BUW48	BUW49		
V <sub>CEV</sub>	Collector-Emitter Voltage (V <sub>BE</sub> = -1.5 V)	120	160	V	
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)	60	80	V	
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)		7		
Ic	Collector Current	3	30		
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> < 5 ms)	ollector Peak Current (t <sub>p</sub> < 5 ms) 45 40		Α	
I <sub>B</sub>	Base Current	8	6	Α	
I <sub>BM</sub>	Base Peak Current (t <sub>p</sub> < 5 ms)	ase Peak Current (t <sub>p</sub> < 5 ms) 12 10		Α	
Ptot	Total Dissipation at T <sub>c</sub> = 25 °C	1:	150		
T <sub>stg</sub>	Storage Temperature	-65 t	-65 to 175		
Tj	Max. Operating Junction Temperature	175		°C	

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## **BUW48 BUW49**

### THERMAL DATA

R <sub>thj-case</sub> Thermal Resistance Junction-case	Max	1	°C/W	
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## **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I <sub>CEX</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5V	$V_{CE} = V_{CEX}$ $V_{CE} = V_{CEX}$ $T_{C} = 125^{\circ}C$			1 3	mA mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			1	mA
V <sub>CEO(sus)</sub> *	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 0.2A L = 25 mH for <b>BUW48</b> for <b>BUW49</b>	60 80			V
V <sub>EBO</sub>	Emitter-base Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 50 mA	7			V
VCE(sat)*	Collector-Emitter Saturation Voltage	$\begin{array}{cccccccccccccccccccccccccccccccccccc$			0.6 1.4 0.5 1.2	V V V
V <sub>BE(sat)</sub> *	Base-Emitter Saturation Voltage	$I_C = 40A$ $I_B = 4A$ for <b>BUW48</b> $I_C = 30A$ $I_B = 3A$ for <b>BUW49</b>			2.1 2	V V
f <sub>T</sub>	Transition Frequency	$I_C = 1A$ $V_{CE} = 15V$ $f = 15$ MHz		8		MHz

### RESISTIVE LOAD

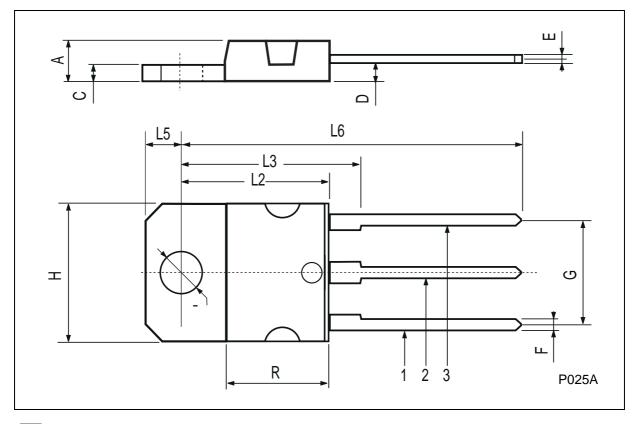
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
t <sub>on</sub> t <sub>s</sub> t <sub>f</sub>	Turn-on Time Storage Time Fall Time	for BUW48 V <sub>CC</sub> = 60V I <sub>B1</sub> = -I <sub>B2</sub> = 4A	I <sub>C</sub> = 40A		1.2 0.6 0.17	1.5 1.1 0.25	μs μs μs
t <sub>s</sub> t <sub>f</sub>	Storage Time Fall Time	for BUW48 V <sub>CC</sub> = 60V I <sub>B1</sub> = -I <sub>B2</sub> = 4A	I <sub>C</sub> = 40A T <sub>C</sub> =100°C			1.65 0.5	μs μs
t <sub>on</sub> t <sub>s</sub> t <sub>f</sub>	Turn-on Time Storage Time Fall Time	for BUW49 V <sub>CC</sub> = 80V I <sub>B1</sub> = -I <sub>B2</sub> = 4A	I <sub>C</sub> = 30A		0.8 0.6 0.15	1.2 1.1 0.25	μs μs μs
t <sub>s</sub> t <sub>f</sub>	Storage Time Fall Time	for BUW49 V <sub>CC</sub> = 80V I <sub>B1</sub> = -I <sub>B2</sub> = 4	I <sub>C</sub> = 30A T <sub>C</sub> =100°C			1.65 0.5	μs μs

<sup>\*</sup> Pulsed: Pulse duration = 300  $\mu$ s, duty cycle < 1.5 %

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# TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch			
<b>D</b> 11111.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.7		4.9	0.185		0.193	
С	1.17		1.37	0.046		0.054	
D		2.5			0.098		
Е	0.5		0.78	0.019		0.030	
F	1.1		1.3	0.043		0.051	
G	10.8		11.1	0.425		0.437	
Н	14.7		15.2	0.578		0.598	
L2	_		16.2	_		0.637	
L3		18			0.708		
L5	3.95		4.15	0.155		0.163	
L6		31			1.220		
R	_		12.2	_		0.480	
Ø	4		4.1	0.157		0.161	



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